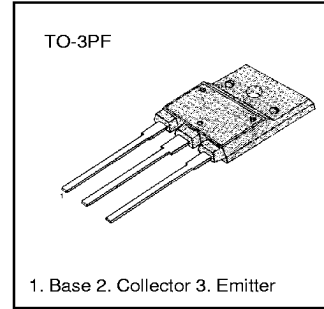


NPN TRIPLE DIFFUSED BU508AF PLANAR SILICON TRANSISTOR

TV HORIZONTAL OUTPUT APPLICATIONS

ABSOLUTE MIXIMUM RATING

Characteristic	Symbol	Rating	Unit
Collector Emitter Voltage	V_{CES}	1500	V
Collector Emitter Voltage	V_{CEO}	700	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	5	A
Collector Current (Pulse)	I_C	15	A
Collector Dissipation ($T_C=25^\circ\text{C}$)	P_C	60	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-65 ~ 150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
*Collector Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C = 100\text{mA}, I_B = 0$	700			V
Emitter Base Voltage	V_{EBO}	$I_E = 10\text{mA}, I_C = 0$	5			V
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}, V_{BE} = 0$			1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			10	mA
*DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 4.5\text{A}$	2.25			
*Collector Emitter Saturation Voltage : BU508AF	$V_{CE(sat)}$	$I_C = 4.5\text{A}, I_B = 2\text{A}$			1	V
*Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 4.5\text{A}, I_B = 2\text{A}$			1.5	V

* Pulse Test: PW = 300 μs , duty cycle = 1.5% Pulsed